



N-Channel 40-V (D-S) MOSFET

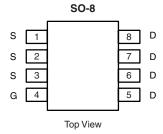
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$ I_D			
40	0.009 at V _{GS} = 10 V	14		
	0.012 at V _{GS} = 4.5 V	12		

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

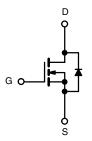


ROHS COMPLIANT HALOGEN FREE



Ordering Information: Si4840DY-T1-E3 (Lead (Pb)-free)

Si4840DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V_{DS}	40		V	
Gate-Source Voltage		V _{GS}	± 20			
Continuous Dunin Comment /T 150 90/8	T _A = 25 °C	- I _D	14	10		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		11	8	A	
Pulsed Drain Current		I _{DM}	50		А	
Avalanche Current	L = 0.1 mH	I _{AS}	30			
Avalanche Energy (Single Pulse)	L = 0.1 IIII	E _{AS}	45		mJ	
Continuous Source Current (Diode Conduction) ^a		I _S	2.8	1.4	А	
M	T _A = 25 °C	- P _D	3.1	1.56	W	
Maximum Power Dissipation ^a	T _A = 70 °C		2.0	1.0	l vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum haration to Austrianta	t ≤ 10 s	R _{thJA}	33	40	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		65	80		
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	21		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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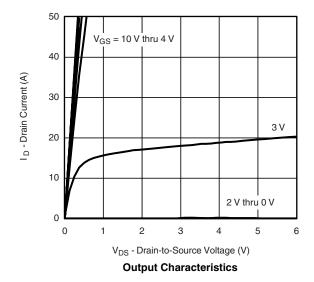
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0		3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V	= 40 V, V _{GS} = 0 V		1		
		$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5	- μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α	
Drain-Source On-State Resistance ^a	В	V _{GS} = 10 V, I _D = 14 A	o = 14 A 0.0075		0.009	Ω	
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 12 \text{ A}$		0.0095	0.012		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 14 A		50		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 2.8 A, V _{GS} = 0 V		0.75	1.1	V	
Dynamic ^b	'		'				
Total Gate Charge	Q_g			18.5	28		
Gate-Source Charge	Q_{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 14 \text{ A}$		6		nC	
Gate-Drain Charge	Q_{gd}			7.5		1	
Gate Resistance	R_g		0.2	0.8	1.2	Ω	
Turn-On Delay Time	t _{d(on)}			15	30		
Rise Time	t _r			10	20	ns	
Turn-Off Delay Time	t _{d(off)}			50	100		
Fall Time	t _f			20	40		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.8 A, dI/dt = 100 A/μs		30	60		

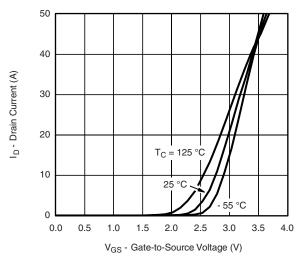
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



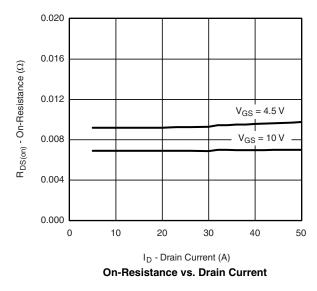


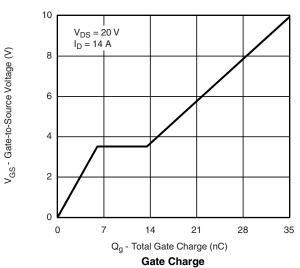




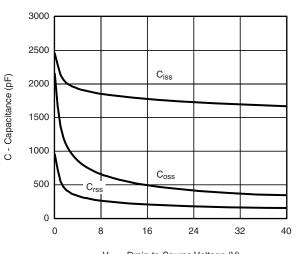


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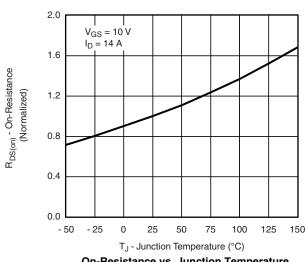




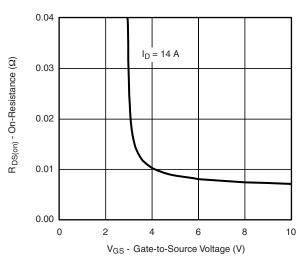
50 T_J = 150 °C 10 T_J = 25 °C 0.0 0.2 0.4 0.6 0.8 1.0 1.2 V_{SD} - Source-to-Drain Voltage (V) Source-Drain Diode Forward Voltage



V_{DS} - Drain-to-Source Voltage (V) Capacitance



On-Resistance vs. Junction Temperature



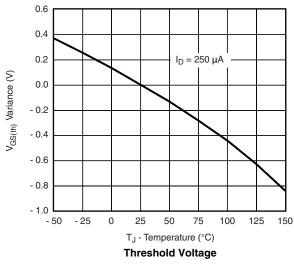
On-Resistance vs. Gate-to-Source Voltage

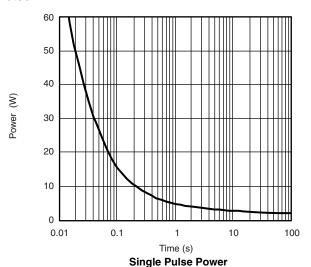
Is - Source Current (A)

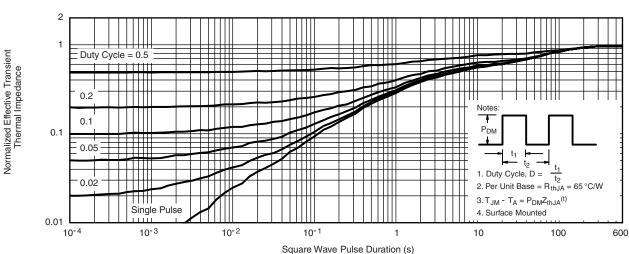
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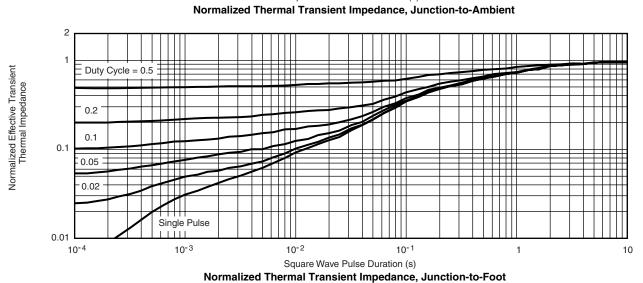
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted









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